

# Steven Chuang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/12044799/publications.pdf>

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13  
papers

3,421  
citations

687220

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docs citations

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times ranked

5673  
citing authors

#	ARTICLE	IF	CITATIONS
1	High-Performance Single Layered WSe <sub>2</sub> p-FETs with Chemically Doped Contacts. Nano Letters, 2012, 12, 3788-3792.	4.5	1,547
2	MoS <sub>2</sub> P-type Transistors and Diodes Enabled by High Work Function MoO <sub>x</sub> Contacts. Nano Letters, 2014, 14, 1337-1342.	4.5	487
3	Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors. Nature, 2010, 468, 286-289.	13.7	373
4	High-Gain Inverters Based on WSe <sub>2</sub> Complementary Field-Effect Transistors. ACS Nano, 2014, 8, 4948-4953.	7.3	284
5	Hole Contacts on Transition Metal Dichalcogenides: Interface Chemistry and Band Alignments. ACS Nano, 2014, 8, 6265-6272.	7.3	173
6	Ballistic InAs Nanowire Transistors. Nano Letters, 2013, 13, 555-558.	4.5	155
7	Nanoscale InGaSb Heterostructure Membranes on Si Substrates for High Hole Mobility Transistors. Nano Letters, 2012, 12, 2060-2066.	4.5	85
8	Ultrathin body InAs tunneling field-effect transistors on Si substrates. Applied Physics Letters, 2011, 98, .	1.5	76
9	Near-ideal electrical properties of InAs/WSe <sub>2</sub> van der Waals heterojunction diodes. Applied Physics Letters, 2013, 102, .	1.5	71
10	Patterned p-Doping of InAs Nanowires by Gas-Phase Surface Diffusion of Zn. Nano Letters, 2010, 10, 509-513.	4.5	57
11	Direct growth of single-crystalline III-V semiconductors on amorphous substrates. Nature Communications, 2016, 7, 10502.	5.8	45
12	Benchmarking the performance of ultrathin body InAs-on-insulator transistors as a function of body thickness. Applied Physics Letters, 2011, 99, .	1.5	40
13	Ultrathin-Body High-Mobility InAsSb-on-Insulator Field-Effect Transistors. IEEE Electron Device Letters, 2012, 33, 504-506.	2.2	28